

BIPOLAR ANALOG INTEGRATED CIRCUIT

μ PC1694GR

GENERAL PURPOSE HIGH FREQUENCY WIDEBAND IC FOR FREQUENCY DOWN-CONVERTER

DESCRIPTION

The μ PC1694GR is Silicon monolithic IC for down-converter that is capable of operating up to 1 GHz.

This IC consists of double balanced mixer (DBM), local oscillator and IF amplifier. Furthermore, combination with the μ PC1663G (high-speed video amp) enables it to be applied to a FM demodulation circuit such as DBS tuner.

The package is 14-pin SOP suitable for surface mounting.

FEATURES

- Satisfactory 1% cross-modulation distortion characteristics: $CM = 103 \text{ dB}\mu @ f_{des} = 200 \text{ MHz}$
- Wide band operation: $f \leq 1 \text{ GHz}$
- Easy to connect with varactor diode due to balanced amplifier oscillator
- Single-end push-pull IF amplifier suppresses fluctuation in output impedance
- Supply voltage: 5 V
- Packaged in 14-pin SOP suitable for smaller mounting area

★ APPLICATIONS

- Tuners for TV and VCR

★ ORDERING INFORMATION

| Part Number | Package | Supplying Form |
|-------------------|------------------------------|--|
| μ PC1694GR-E1 | 14-pin plastic SOP (225 mil) | Embossed tape 16 mm wide. Pin 1 indicates pull-out direction of tape. |

Remark To order evaluation samples, please contact your local NEC office.

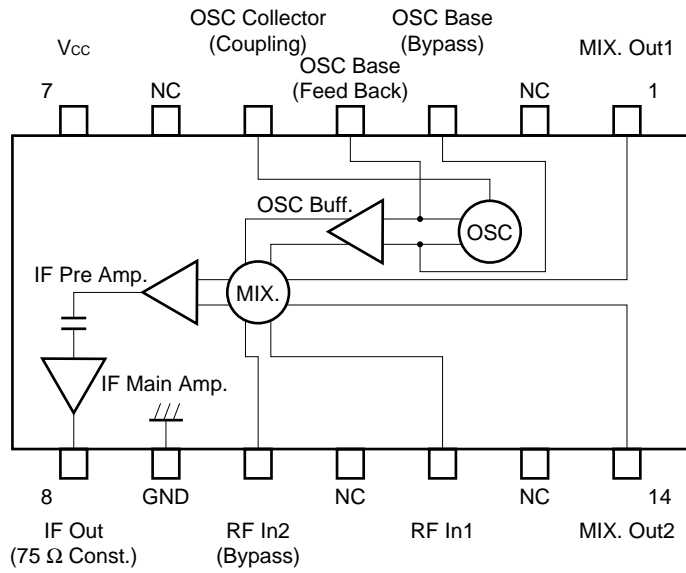
(Part number for sample order: μ PC1694GR)

Caution Electro-static sensitive devices

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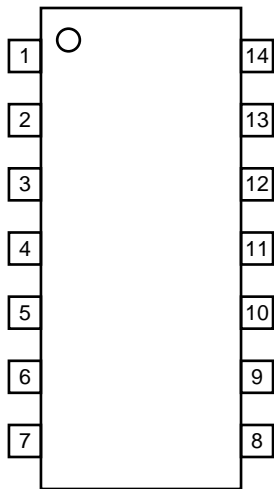
Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

INTERNAL BLOCK DIAGRAM



PIN CONFIGURATION

(Top View)



1. MIX output 1
2. GND (Non Connection)
3. OSC base (bypass)
4. OSC base (feedback)
5. OSC collector (coupling)
(MIX/IF Amp. switch)
6. GND (Non Connection)
7. Vcc
8. IF output (75 Ω)
9. GND
10. RF input 2 (bypass)
11. GND (Non Connection)
12. RF input 1
13. GND (Non Connection)
14. MIX output 2

★ ABSOLUTE MAXIMUM RATINGS (T_A = +25°C)

| Parameter | Symbol | Conditions | Rating | Unit |
|-------------------------------|------------------|------------------------------------|-------------|------|
| Supply Voltage | V _{cc} | | 6.0 | V |
| Power Dissipation | P _d | T _A = +85°C Note | 325 | mW |
| Operating Ambient Temperature | T _A | | -40 to +85 | °C |
| Storage Temperature | T _{stg} | | -65 to +150 | °C |

Note Mounted on 50 × 50 × 1.6-mm epoxy glass PWB, with copper patterning on both sides.

★ RECOMMENDED OPERATING RANGE

| Parameter | Symbol | MIN. | TYP. | MAX. | Unit |
|-------------------------------|-----------------|------|------|------|------|
| Supply Voltage | V _{CC} | 4.5 | 5.0 | 5.5 | V |
| Operating Ambient Temperature | T _A | -40 | +25 | +85 | °C |

ELECTRICAL CHARACTERISTICS (T_A = +25°C, V_{CC} = 5 V)

| Parameter | Symbol | Test Conditions | MIN. | TYP. | MAX. | Unit |
|--------------------------|----------------------|---|------|------|------|------|
| Circuit Current 1 | I _{CC1} | No input signal Note 1 | 32 | 40 | 48 | mA |
| Mixer Output Voltage | V _{MIX} | 1-14 pin voltage, No input signal Note 1 | -30 | 0 | +30 | mV |
| Conversion Gain 1 | CG1 | f _{RF} = 55 to 470 MHz, f _{IF} = 50 MHz P _{RF} = -40 dBm RF Input Terminal: Non Tuned Note 2 | 14 | 18 | 21 | dB |
| Conversion Gain 2 | CG2 | f _{RF} = 470 to 890 MHz, f _{IF} = 50 MHz P _{RF} = -40 dBm RF Input Terminal: Non Tuned Note 3 | 14 | 18 | 21 | dB |
| Noise Figure 1 | NF1 | f _{RF} = 55 to 470 MHz, f _{IF} = 50 MHz RF Input Terminal: Non Tuned Note 2 | — | 12.5 | 15.0 | dB |
| Noise Figure 2 | NF2 | f _{RF} = 470 to 890 MHz, f _{IF} = 50 MHz RF Input Terminal: Non Tuned Note 3 | — | 13.5 | 16.0 | dB |
| Output Power 1 | P _{O(sat)1} | f _{RF} = 470 MHz, f _{IF} = 50 MHz, P _{RF} = 0 dBm Note 2 | +8 | +10 | — | dBm |
| Output Power 2 | P _{O(sat)2} | f _{RF} = 890 MHz, f _{IF} = 50 MHz, P _{RF} = 0 dBm Note 3 | +8 | +10 | — | dBm |
| Circuit Current 2 (U/IF) | I _{CC2} | No input signal Note 1 | 32 | 40 | 48 | mA |
| Power Gain (U/IF) | G _P | f _{in} = 50 MHz, P _{in} = -40 dBm Note 2 | 17 | 21 | 24 | dB |
| Noise Figure 3 (U/IF) | NF3 | f _{in} = 50 MHz Note 2 | — | 12.0 | 15.0 | dB |

- Notes 1.** By test circuit 1
- 2.** By test circuit 2
- 3.** By test circuit 3

STANDARD CHARACTERISTICS (FOR REFERENCE) (T_A = +25°C, V_{CC} = 5 V)

| Parameter | Symbol | Test Conditions | Reference Value | Unit |
|---|-------------------|--|-----------------|------|
| Conversion Gain 3 | CG3 | f _{RF} = 55 MHz, f _{IF} = 50 MHz, P _{RF} = -40 dBm RF Input Terminal: Tuned Note 1 | 24.5 | dB |
| Conversion Gain 4 | CG4 | f _{RF} = 200 MHz, f _{IF} = 50 MHz, P _{RF} = -40 dBm RF Input Terminal: Tuned Note 1 | 24.5 | dB |
| Conversion Gain 5 | CG5 | f _{RF} = 470 MHz, f _{IF} = 50 MHz, P _{RF} = -40 dBm RF Input Terminal: Tuned Note 1 | 23.0 | dB |
| Conversion Gain 6 | CG6 | f _{RF} = 890 MHz, f _{IF} = 50 MHz, P _{RF} = -40 dBm RF Input Terminal: Tuned Note 2 | 20.0 | dB |
| 1% Cross-modulation Distortion 1 | CM1 | f _{RF} = 55 to 470 MHz, f _{IF} = 50 MHz Note 1, 3 | 103 | dBμ |
| 1% Cross-modulation Distortion 2 | CM2 | f _{RF} = 470 to 890 MHz, f _{IF} = 50 MHz Note 2, 3 | 100 | dBμ |
| 1% Cross-modulation Distortion 3 (U/IF) | CM3 | f _{RF} = 50 MHz Note 1, 4 | 103 | dBμ |
| Oscillation Frequency Stability 1 | f _{stb1} | V _{CC} ± 10%, f _{osc} = 100 to 520 MHz Note 1 | ±100 | kHz |
| Oscillation Frequency Stability 2 | f _{stb2} | V _{CC} ± 10%, f _{osc} = 520 to 940 MHz Note 2 | ±200 | |
| Oscillation Stop (Start) Voltage 1 | V _{osc1} | f _{osc} = 100 to 520 MHz Note 1 | 2.5 | V |
| Oscillation Stop (Start) Voltage 2 | V _{osc2} | f _{osc} = 520 to 940 MHz Note 2 | 3.0 | |

Notes 1. By test circuit 2

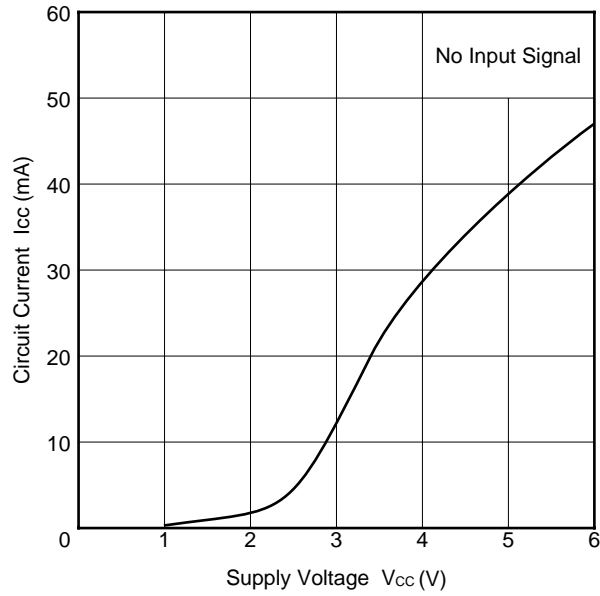
2. By test circuit 3

3. f_{undes} = f_{RF} ± 12 MHz, P_{RF} = -31 dBm, f_{IF} = 50 MHz, AM: 100 kHz, 30%Mod., S/I Ratio = 46 dBc, Output 75 Ω Open

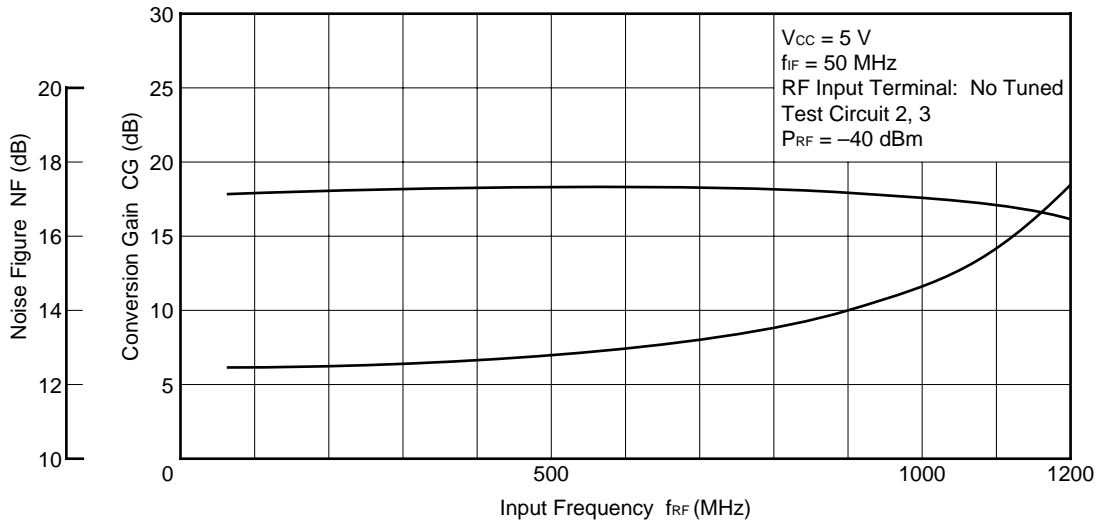
4. f_{in} = 50 MHz, f_{undes} = 62 MHz, P_{in} = -31 dBm, AM: 100 kHz, 30% Mod., S/I Ratio = 46 dBc, Output 75 Ω Open

TYPICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$)

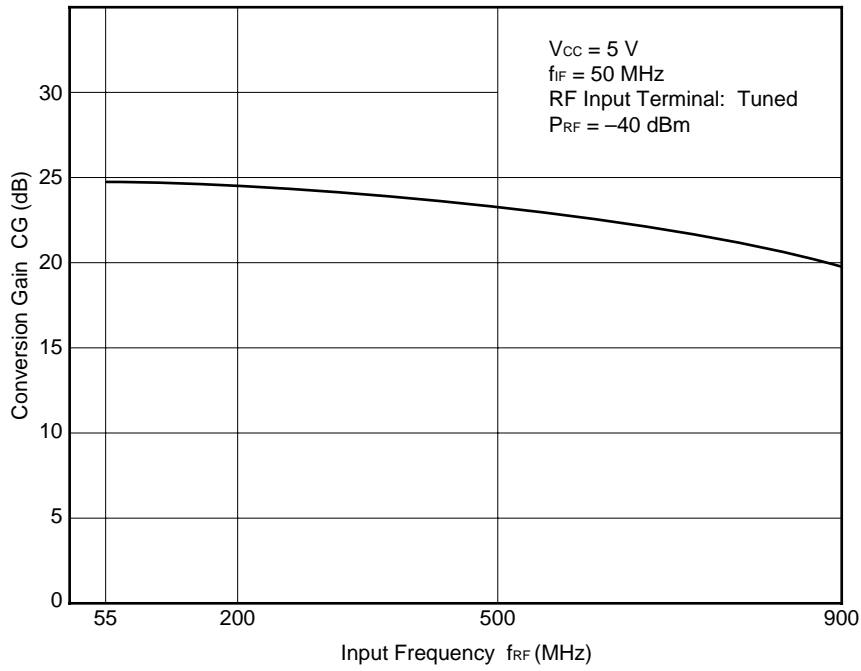
CIRCUIT CURRENT vs. SUPPLY VOLTAGE



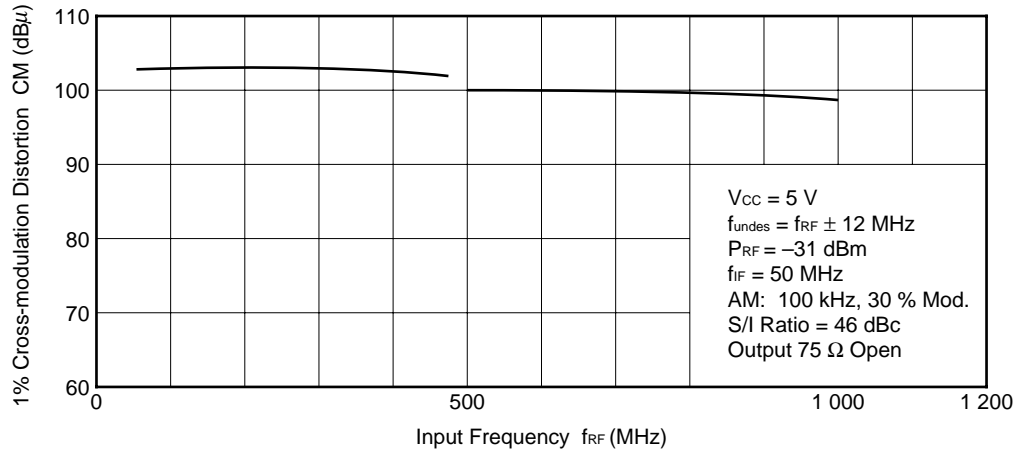
NOISE FIGURE AND CONVERSION GAIN vs. INPUT FREQUENCY

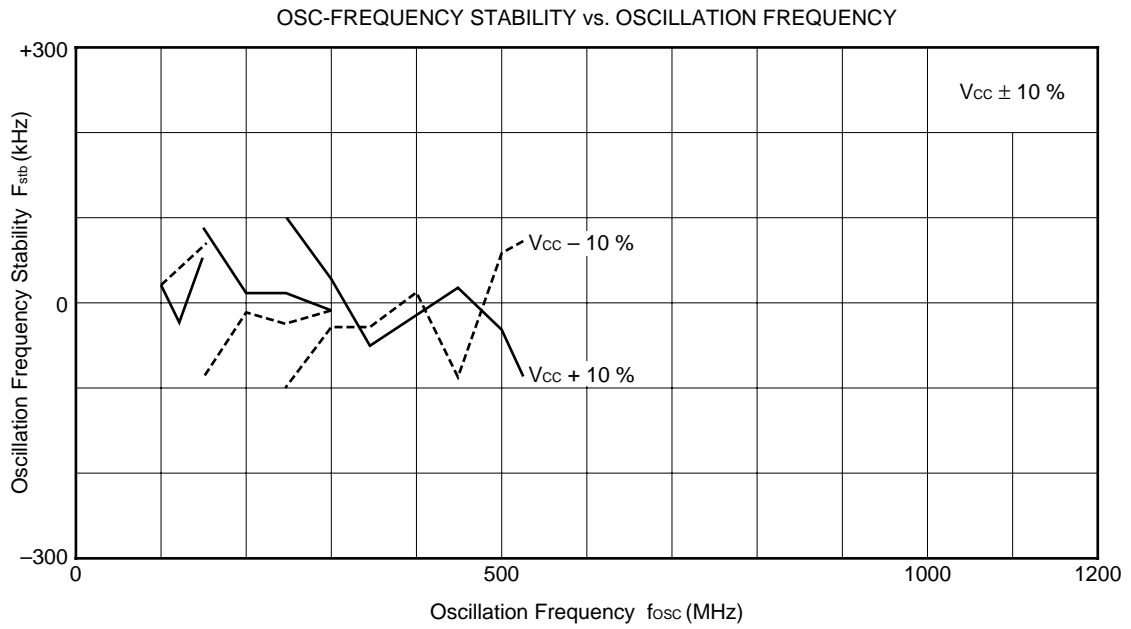
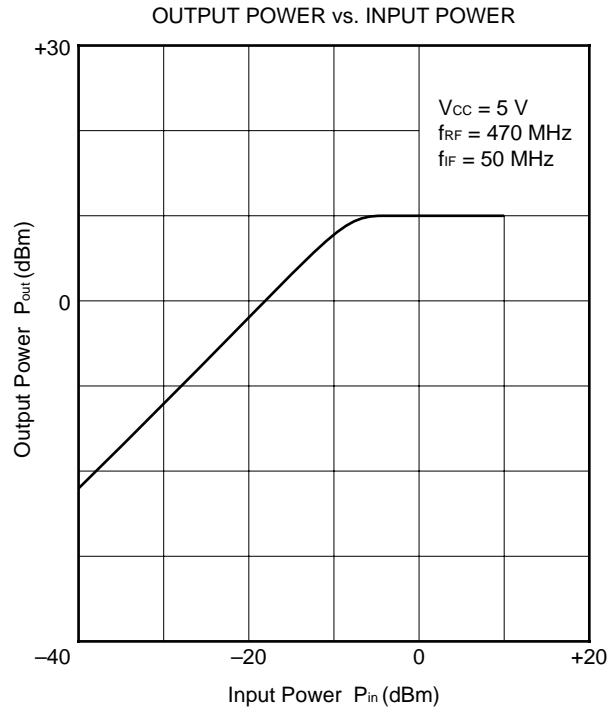


CONVERSION GAIN vs. INPUT FREQUENCY

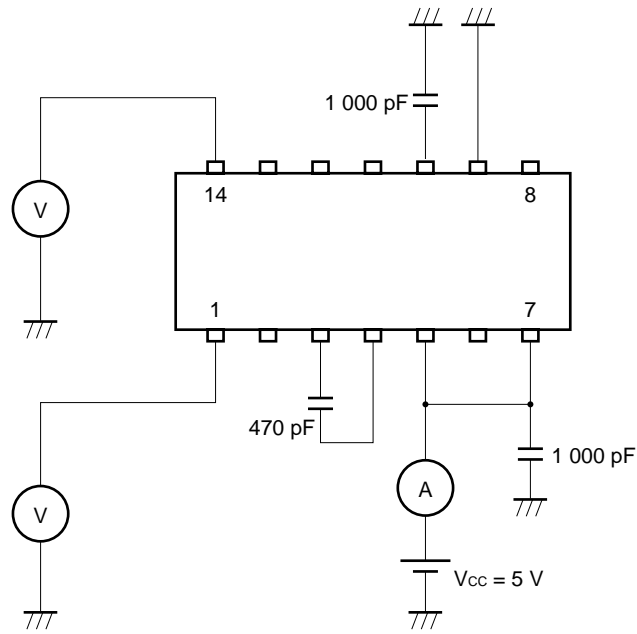


1% CROSS-MODULATION DISTORTION vs. INPUT FREQUENCY



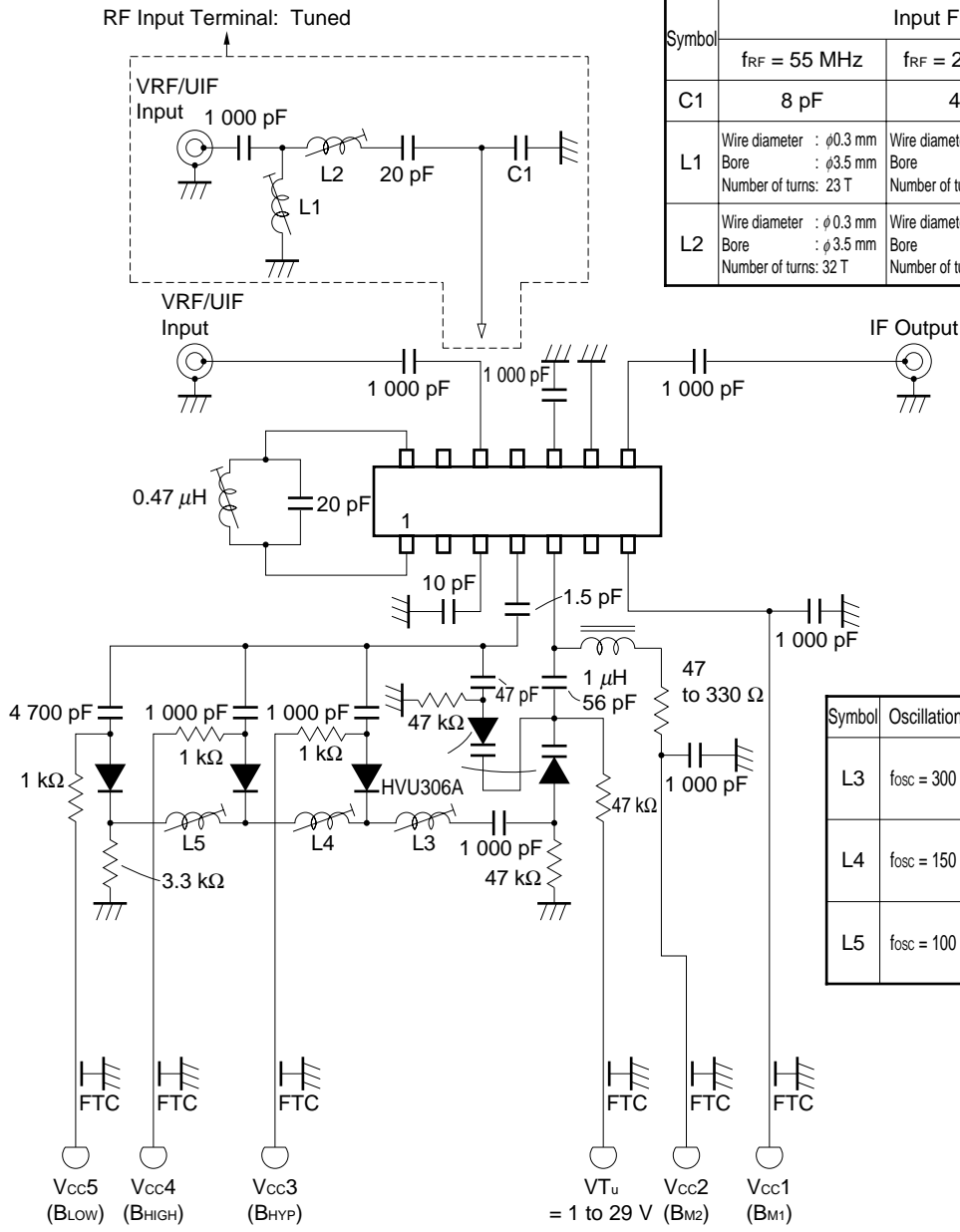


TEST CIRCUIT 1



When measuring circuit current with U/IF Amp, leave pin 5 open.

TEST CIRCUIT 2

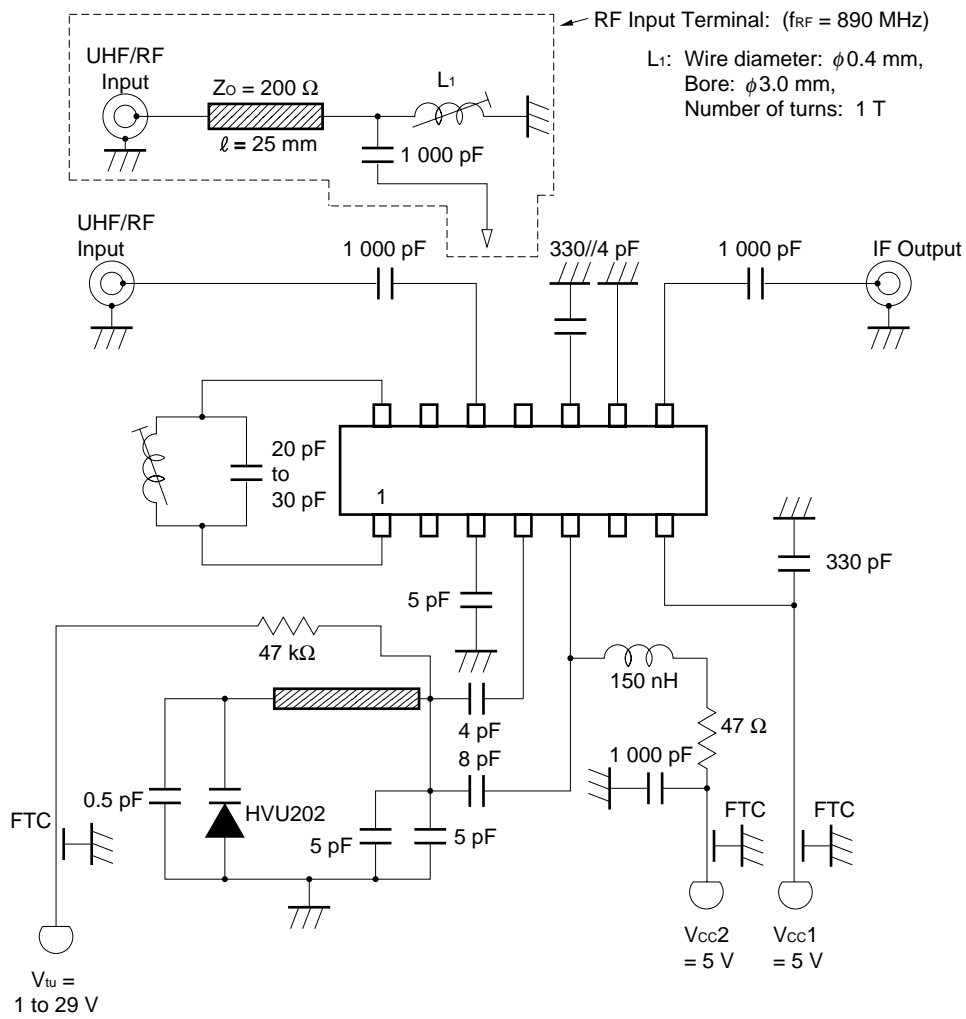


| Symbol | Input Frequency | | |
|--------|--|---|---|
| | $f_{RF} = 55 \text{ MHz}$ | $f_{RF} = 200 \text{ MHz}$ | $f_{RF} = 470 \text{ MHz}$ |
| C1 | 8 pF | 4 pF | 2 pF |
| L1 | Wire diameter : $\phi 0.3 \text{ mm}$ Bore : $\phi 3.5 \text{ mm}$ Number of turns: 23 T | Wire diameter : $\phi 0.4 \text{ mm}$ Bore : $\phi 3.2 \text{ mm}$ Number of turns: 3 T | Wire diameter : $\phi 0.4 \text{ mm}$ Bore : $\phi 3.5 \text{ mm}$ Number of turns: 2 T |
| L2 | Wire diameter : $\phi 0.3 \text{ mm}$ Bore : $\phi 3.5 \text{ mm}$ Number of turns: 32 T | Wire diameter : $\phi 0.3 \text{ mm}$ Bore : $\phi 4.0 \text{ mm}$ Number of turns: 7 T | Wire diameter : $\phi 0.5 \text{ mm}$ Bore : $\phi 3.5 \text{ mm}$ Number of turns: 2 T |

| Symbol | Oscillation Frequency | Coil used |
|--------|---|---|
| L3 | $f_{osc} = 300 \text{ to } 520 \text{ MHz}$ | Wire diameter : $\phi 0.5 \text{ mm}$ Bore : $\phi 3.0 \text{ mm}$ Number of turns: 2 T |
| L4 | $f_{osc} = 150 \text{ to } 300 \text{ MHz}$ | Wire diameter : $\phi 0.4 \text{ mm}$ Bore : $\phi 2.5 \text{ mm}$ Number of turns: 3 T |
| L5 | $f_{osc} = 100 \text{ to } 150 \text{ MHz}$ | Wire diameter : $\phi 0.4 \text{ mm}$ Bore : $\phi 3.0 \text{ mm}$ Number of turns: 9 T |

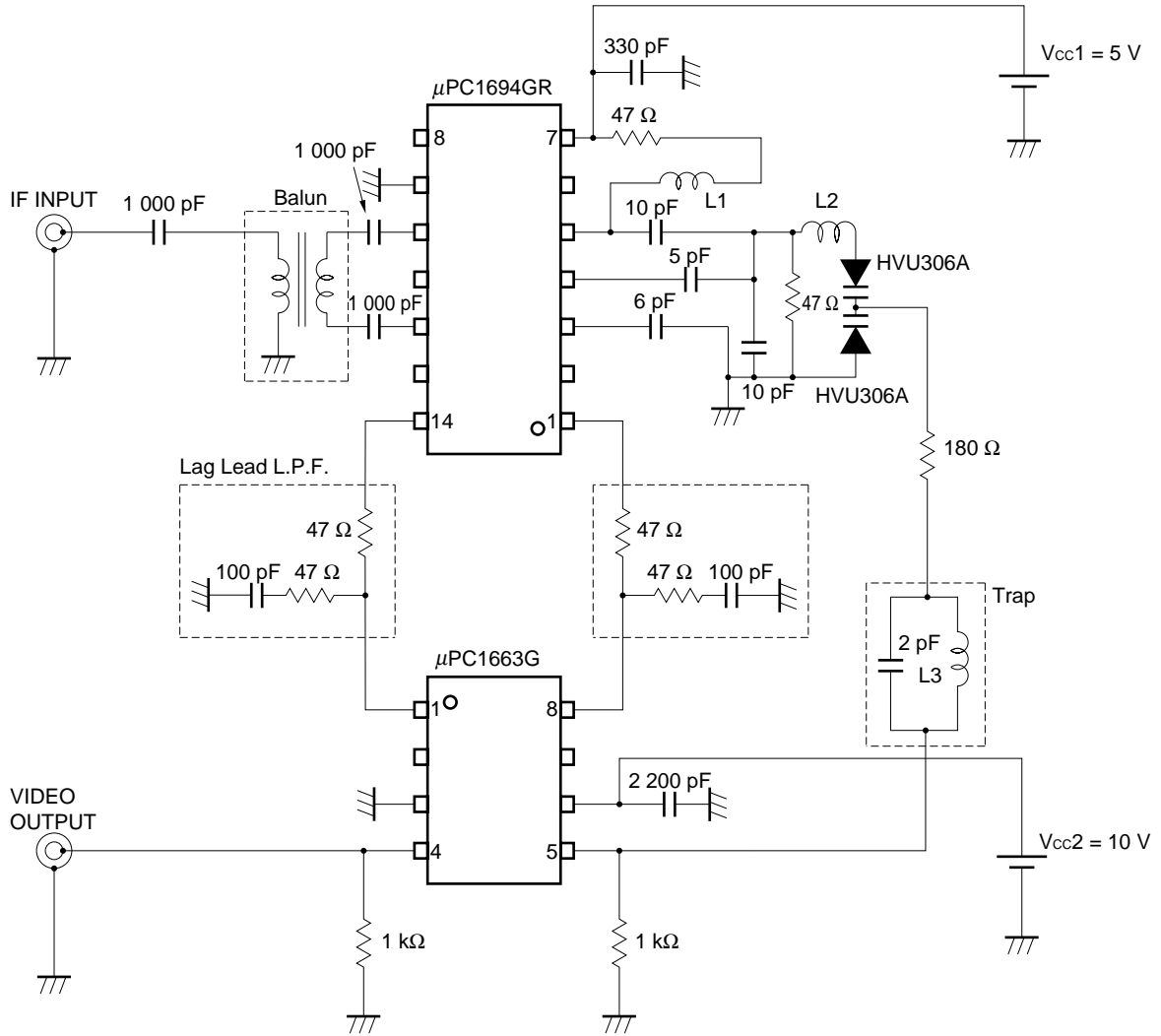
| | Vcc1 (BM1) | Vcc2 (BM2) | Vcc3 (BHYP) | Vcc4 (BHIGH) | Vcc5 (BLOW) |
|--------|---------------|---------------|----------------|-----------------|----------------|
| VLOW | 5 V | 5 V | OPEN | OPEN | 5 V |
| VHIGH | 5 V | 5 V | OPEN | 5 V | OPEN |
| VHYPER | 5 V | 5 V | 5 V | OPEN | OPEN |
| U/IF | 5 V | OPEN | OPEN | OPEN | OPEN |

TEST CIRCUIT 3



APPLICATION CIRCUIT EXAMPLE 1

For FM demodulator (Example using μ PC1694GR and μ PC1663G)



- L1: Wire diameter: ϕ 0.3 mm, Bore: ϕ 1.5 mm, Number of turns: 13 T
- L2: Wire diameter: ϕ 0.4 mm, Bore: ϕ 3.5 mm, Number of turns: 2 T
- L3: Wire diameter: ϕ 0.3 mm, Bore: ϕ 1.8 mm, Number of turns: 7 T
- Balun: TDK WBT5,5P5-C10129E

APPLICATION CIRCUIT EXAMPLE 2

For TV/VCR TUNER

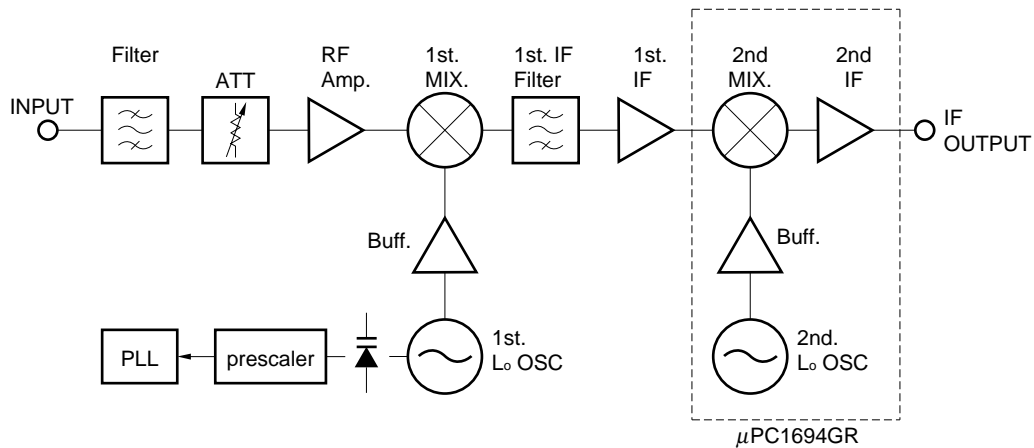
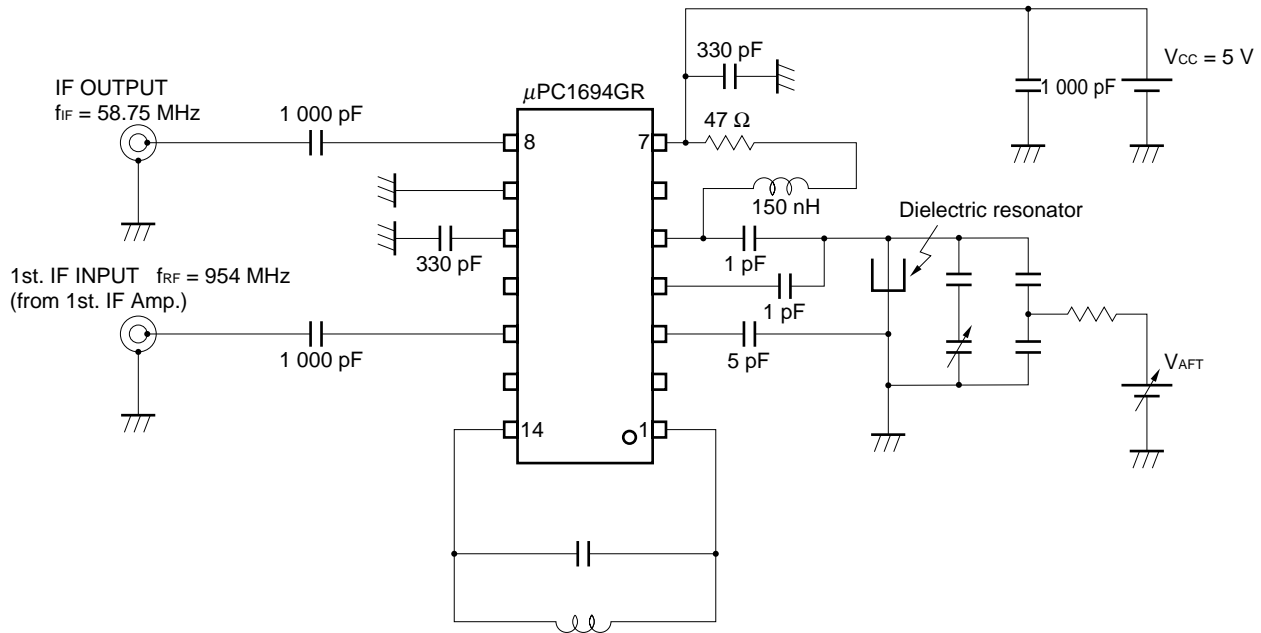
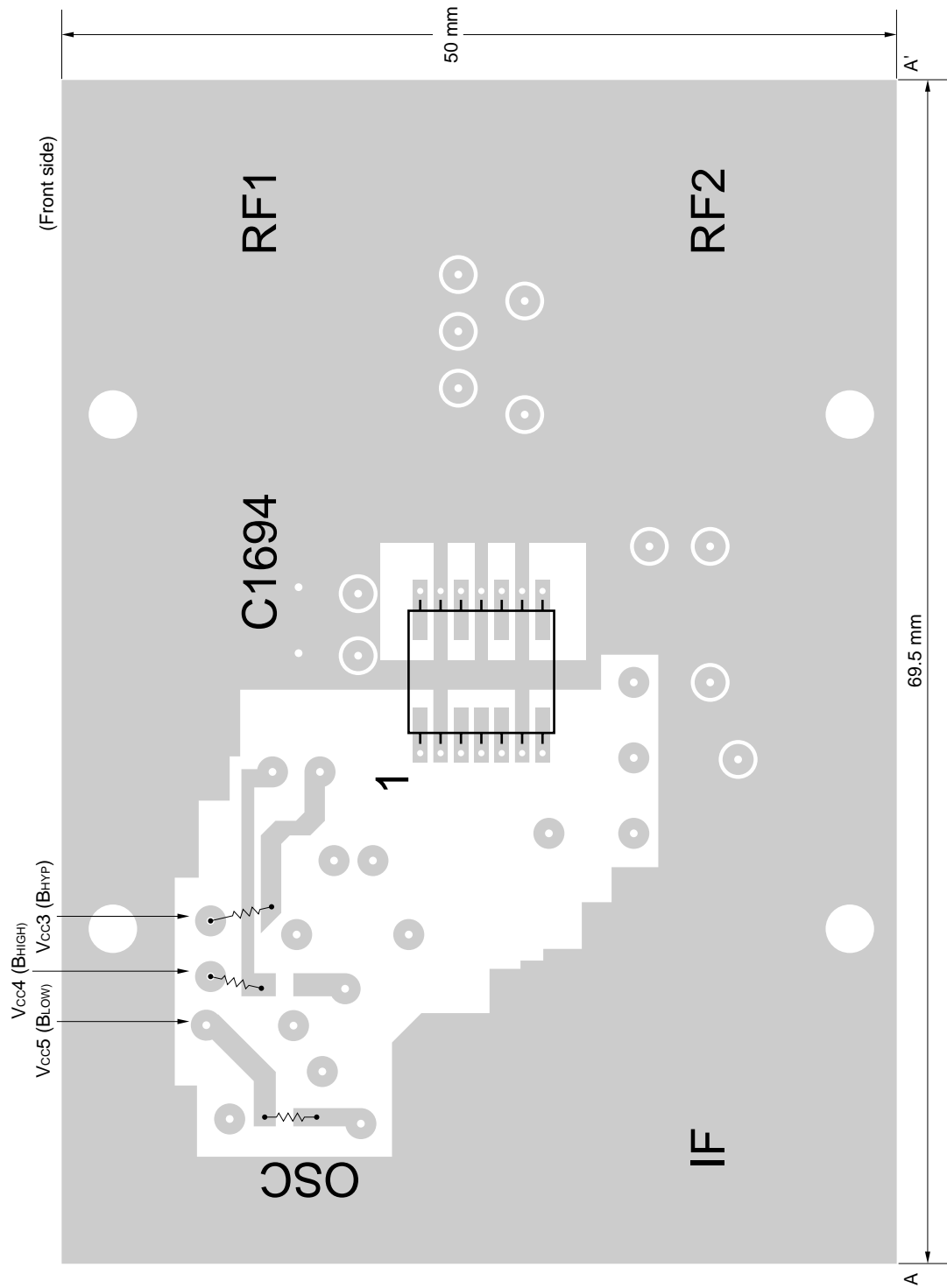
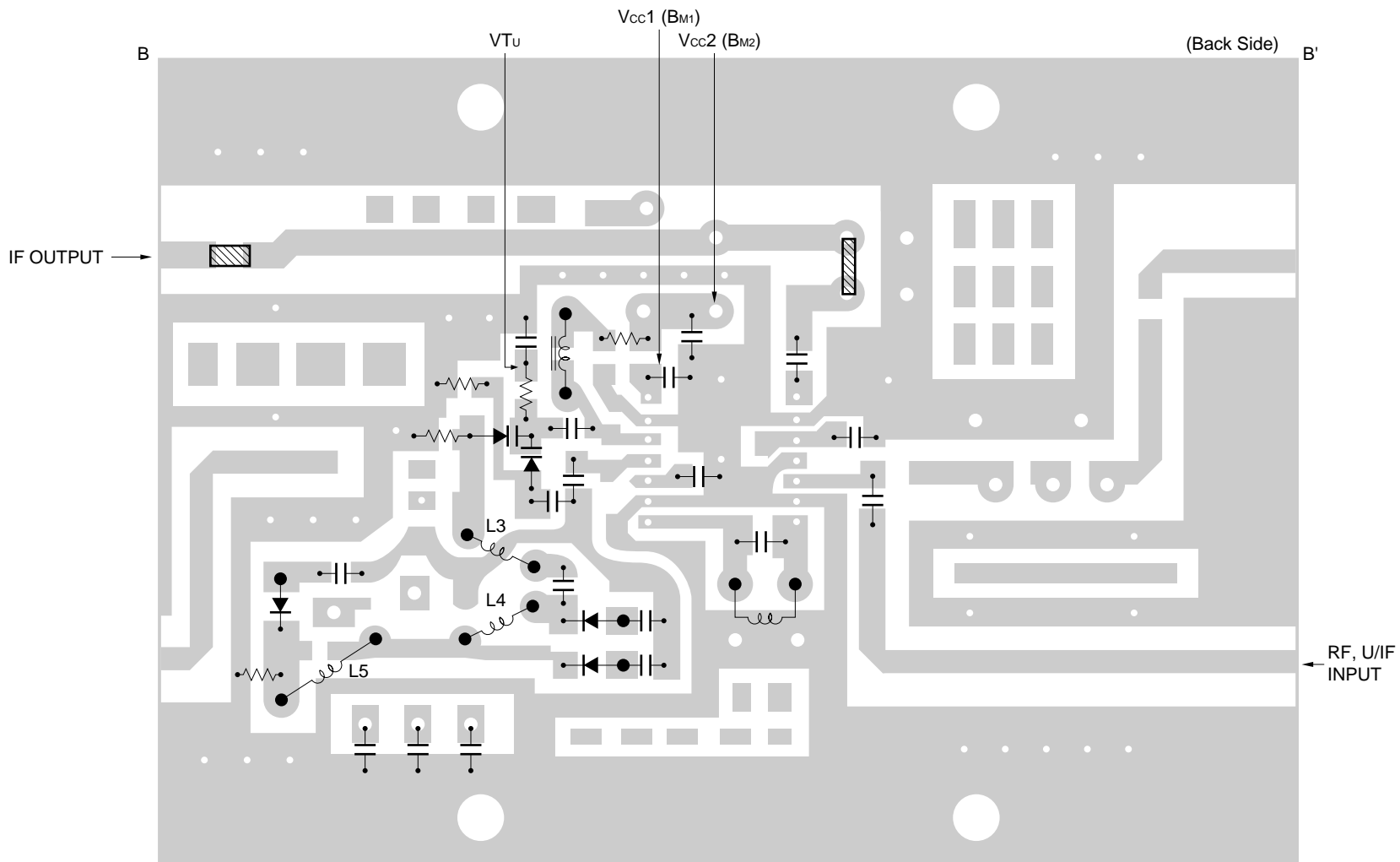


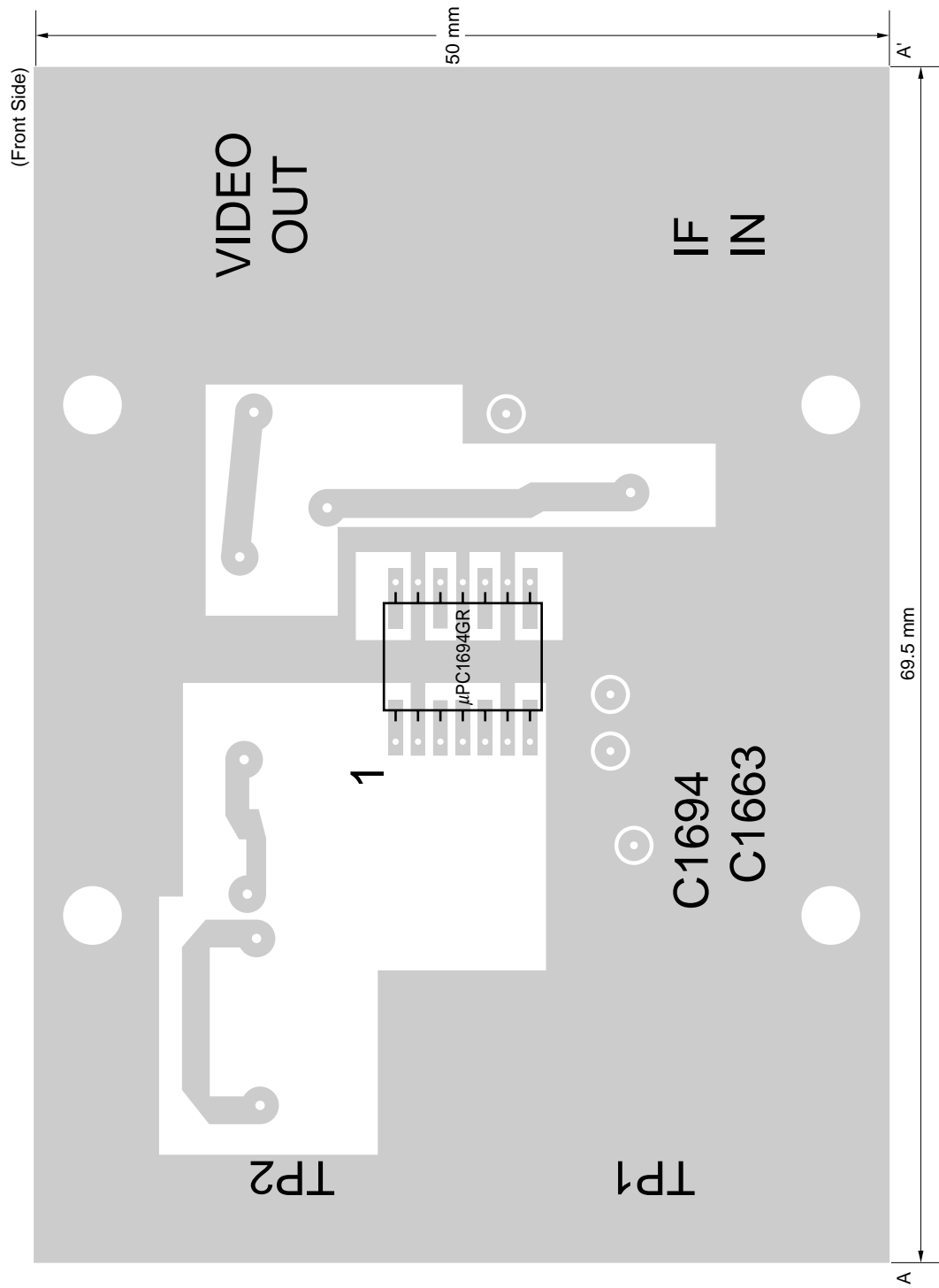
ILLUSTRATION OF THE APPLICATION CIRCUIT EXAMPLE 2 ASSEMBLED ON EVALUATION BOARD

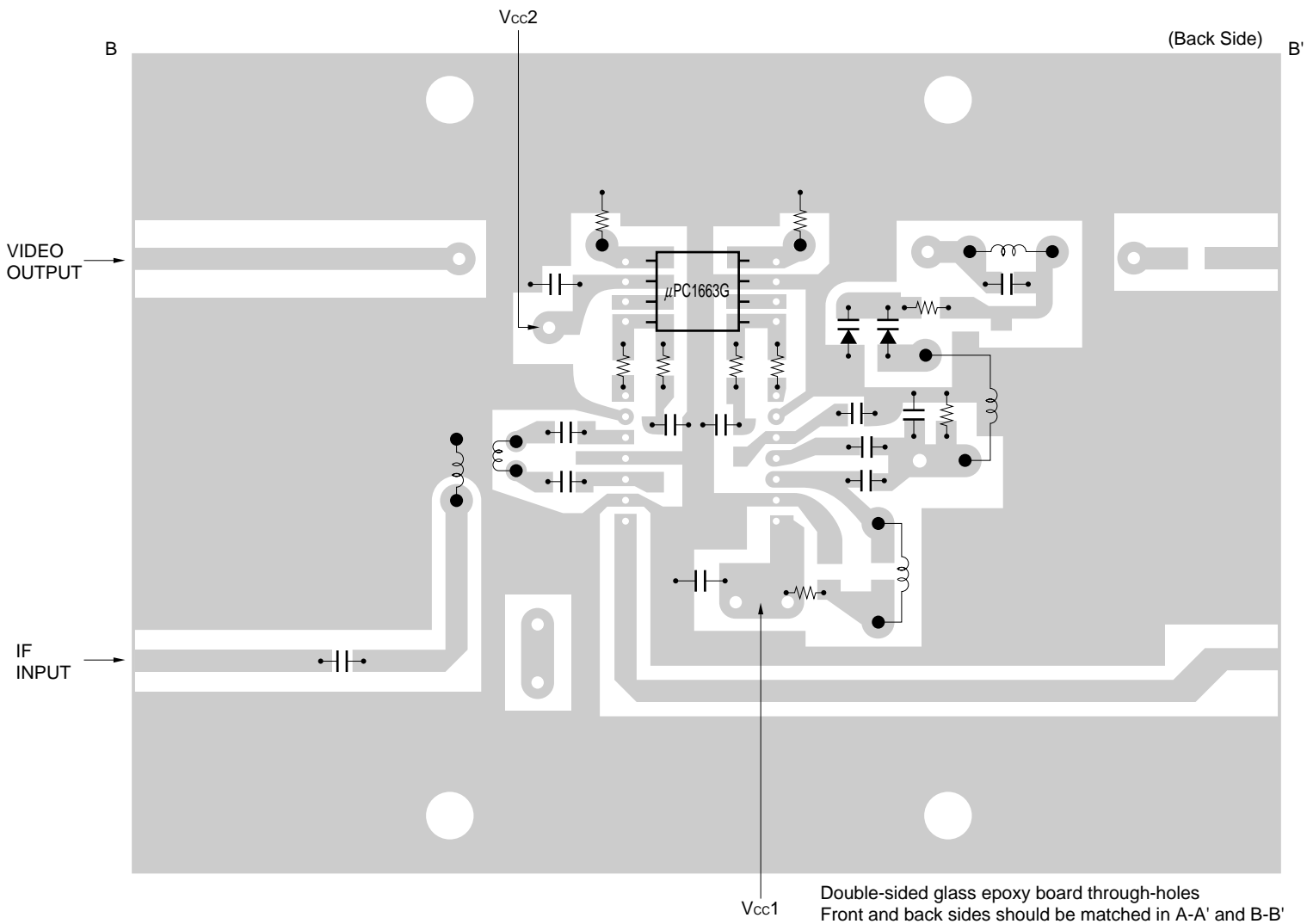




Double-sided glass epoxy board through-holes
 Front and back sides should be matched in A-A' and B-B'
 ▨: short-circuited strip.

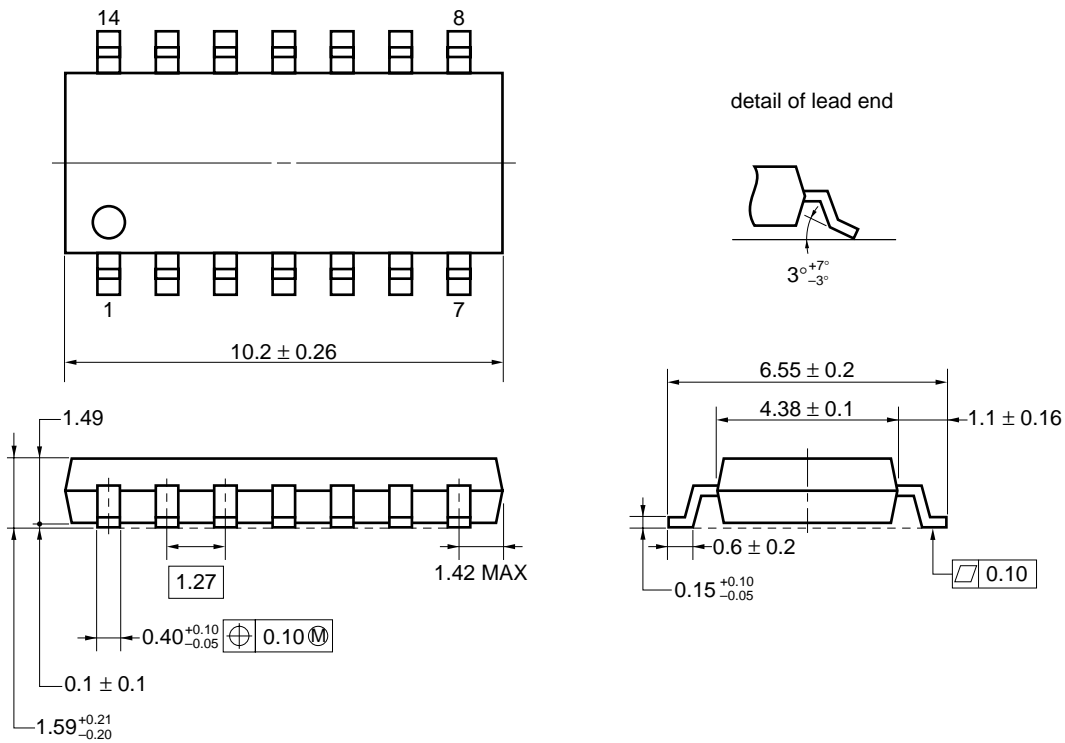
ILLUSTRATION OF THE APPLICATION CIRCUIT EXAMPLE 1 ASSEMBLED ON EVALUATION BOARD





★ PACKAGE DIMENSION

14 PIN PLASTIC SOP (225 mil)



NOTE Each lead centerline is located within 0.10 mm of its true position (T.P.) at maximum material condition.

NOTE ON CORRECT USE

- (1) Since this IC uses high frequency process, care is required against the excessive input of static electricity, etc.
- (2) Use the shortest possible wiring for the GND pin.
- (3) Use the widest possible earth pattern to avoid increase of ground impedance (because it may cause abnormal oscillation).
- (4) Insert a bypass capacitor for the V_{cc} pin (example: 1 000 pF, 2 200 pF, etc.)
- (5) Abnormal oscillation may occur depending on the values of the choke coil and floating capacitance. Therefore, insert a resistor between the power supply and choke coil. (See the application circuit example.)

RECOMMENDED SOLDERING CONDITIONS

This product should be soldered under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your NEC sales representative.

| Soldering Method | Soldering Conditions | Recommended Condition Symbol |
|------------------|---|------------------------------|
| Infrared Reflow | Package peak temperature: 235 °C or below Time: 30 seconds or less (at 210 °C) Count: 3, Exposure limit: None ^{Note} | IR35-00-3 |
| VPS | Package peak temperature: 215 °C or below Time: 40 seconds or less (at 200 °C) Count: 3, Exposure limit: None ^{Note} | VP15-00-3 |
| Wave Soldering | Soldering bath temperature: 260 °C or below Time: 10 seconds or less Count: 1, Exposure limit: None ^{Note} | WS60-00-1 |
| Partial Heating | Pin temperature: 300 °C Time: 3 seconds or less (per side of device) Exposure limit: None ^{Note} | — |

Note After opening the dry pack, keep it in a place below 25 °C and 65 % RH for the allowable storage period.

Caution Do not use different soldering methods together (except for partial heating).

For details of recommended soldering conditions for surface mounting, refer to information document SEMICONDUCTOR DEVICE MOUNTING TECHNOLOGY MANUAL (C10535E).

[MEMO]

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